

Dong-Sing Wuu

List of Publications by Year in descending order

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259
papers

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126907

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260
docs citations

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times ranked

4174
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#	ARTICLE	IF	CITATIONS
1	Ga ₂ O ₃ nanorod-based extended-gate field-effect transistors for pH sensing. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2022, 276, 115542.	3.5	12
2	Structural and photodetector characteristics of Zn and Al incorporated ZnGa ₂ O ₄ films via co-sputtering. <i>Results in Physics</i> , 2022, 33, 105206.	4.1	8
3	Annealing temperature controlled crystallization mechanism and properties of gallium oxide film in forming gas atmosphere. <i>Journal of the American Ceramic Society</i> , 2022, 105, 4487-4499.	3.8	6
4	Study on the effect of size on InGaN red micro-LEDs. <i>Scientific Reports</i> , 2022, 12, 1324.	3.3	41
5	Improved Characteristics of CdSe/CdS/ZnS Core-Shell Quantum Dots Using an Oleylamine-Modified Process. <i>Nanomaterials</i> , 2022, 12, 909.	4.1	7
6	Growth and characterization of Si-doped Ga ₂ O ₃ thin films by remote plasma atomic layer deposition: Toward UVC-LED application. <i>Surface and Coatings Technology</i> , 2022, 435, 128252.	4.8	7
7	Ion bombardment effect on properties of MoO thin film under different PEALD plasma exposure time. <i>Vacuum</i> , 2022, 200, 111025.	3.5	0
8	Compact Ga ₂ O ₃ Thin Films Deposited by Plasma Enhanced Atomic Layer Deposition at Low Temperature. <i>Nanomaterials</i> , 2022, 12, 1510.	4.1	10
9	Thermal behavior of AlGaN-based deep-UV LEDs. <i>Optics Express</i> , 2022, 30, 16827.	3.4	6
10	Pulsed laser deposition grown non-stoichiometry transferred ZnGa ₂ O ₄ films for deep-ultraviolet applications. <i>Applied Surface Science</i> , 2022, 597, 153700.	6.1	10
11	Oxygen annealing induced crystallization and cracking of pulsed laser deposited Ga ₂ O ₃ films. <i>Vacuum</i> , 2022, 202, 111176.	3.5	10
12	Synthesis of SiO ₂ -coated CdSe/ZnS quantum dots using various dispersants in the photoresist for color-conversion micro-LED displays. <i>Materials Science in Semiconductor Processing</i> , 2022, 148, 106790.	4.0	6
13	Role of Ambient Hydrogen in HiPIMS-ITO Film during Annealing Process in a Large Temperature Range. <i>Nanomaterials</i> , 2022, 12, 1995.	4.1	0
14	Influence of Al doping on crystal structure, optical, and photoluminescence characteristics of ZnGa ₂ O ₄ films. <i>Materials Science in Semiconductor Processing</i> , 2022, 150, 106962.	4.0	7
15	Improvement in the Figure of Merit of ITO-Metal-ITO Sandwiched Films on Poly Substrate by High-Power Impulse Magnetron Sputtering. <i>Coatings</i> , 2021, 11, 144.	2.6	19
16	Deposition of high-transmittance ITO thin films on polycarbonate substrates for capacitive-touch applications. <i>Vacuum</i> , 2021, 186, 110046.	3.5	9
17	Preparation of AgNWs@NiO@Co ₃ O ₄ dopant material for an activated carbon thin-film electrode of pseudocapacitors. <i>Journal of Materials Science</i> , 2021, 56, 15229-15240.	3.7	7
18	Structural design and performance improvement of flip-chip AlGaInP mini light-emitting diodes. <i>Semiconductor Science and Technology</i> , 2021, 36, 095008.	2.0	7

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19	The Effect of Annealing Ambience on the Material and Photodetector Characteristics of Sputtered ZnGa ₂ O ₄ Films. <i>Nanomaterials</i> , 2021, 11, 2316.	4.1	14
20	Growth and characterization of co-sputtered Al-doped ZnGa ₂ O ₄ films for enhancing deep-ultraviolet photoresponse. <i>Applied Surface Science</i> , 2021, 566, 150714.	6.1	9
21	Enhanced external quantum efficiencies of AlGaIn-based deep-UV LEDs using reflective passivation layer. <i>Optics Express</i> , 2021, 29, 37835.	3.4	17
22	Role of Interfacial Oxide in the Preferred Orientation of Ga ₂ O ₃ on Si for Deep Ultraviolet Photodetectors. <i>ACS Omega</i> , 2021, 6, 29149-29156.	3.5	4
23	High Performance AlGaInP-Based Micro-LED Displays With Novel Pixel Structures. <i>IEEE Photonics Technology Letters</i> , 2021, 33, 1375-1378.	2.5	10
24	Incorporation of Au Nanoparticles on ZnO/ZnS Core Shell Nanostructures for UV Light/Hydrogen Gas Dual Sensing Enhancement. <i>Membranes</i> , 2021, 11, 903.	3.0	3
25	Advanced Atomic Layer Deposition Technologies for Micro-LEDs and VCSELs. <i>Nanoscale Research Letters</i> , 2021, 16, 164.	5.7	12
26	On the mechanism of carrier recombination in downsized blue micro-LEDs. <i>Scientific Reports</i> , 2021, 11, 22788.	3.3	11
27	Impact of thermal-induced sapphire substrate erosion on material and photodetector characteristics of sputtered Ga ₂ O ₃ films. <i>Journal of Alloys and Compounds</i> , 2020, 823, 153755.	5.5	25
28	The role of laser ablated backside contact pattern in efficiency improvement of mono crystalline silicon PERC solar cells. <i>Solar Energy</i> , 2020, 196, 462-467.	6.1	24
29	Zinc Gallium Oxide—A Review from Synthesis to Applications. <i>Nanomaterials</i> , 2020, 10, 2208.	4.1	40
30	Characterization of semi-polar (20 $\overline{2}$ 1) InGaIn microLEDs. <i>Scientific Reports</i> , 2020, 10, 15966.	3.3	7
31	Editorial: The biennial TACT international thin films conference (TACT 2019). <i>Thin Solid Films</i> , 2020, 709, 138210.	1.8	0
32	Growth characteristics of Fe-doped GaN epilayers on SiC (001) substrates and their effects on high breakdown voltage devices. <i>Materials Science in Semiconductor Processing</i> , 2020, 119, 105228.	4.0	4
33	Nitrogen and oxygen annealing effects on properties of aluminum-gallium oxide films grown by pulsed laser deposition. <i>Ceramics International</i> , 2020, 46, 24147-24154.	4.8	12
34	Special Issue Editorial: Functional Oxide Based Thin-Film Materials. <i>Crystals</i> , 2020, 10, 195.	2.2	0
35	Improved Performance of Passive-Matrix Micro-LED Displays Using a Multi-Function Passivation Structure. <i>IEEE Photonics Journal</i> , 2020, 12, 1-11.	2.0	8
36	Process Integration and Interconnection Design of Passive-Matrix LED Micro-Displays With 256 Pixel-Per-Inch Resolution. <i>IEEE Journal of the Electron Devices Society</i> , 2020, 8, 251-255.	2.1	10

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37	Improvement of p-electrode structures for 280 nm AlGaIn LED applications. <i>Semiconductor Science and Technology</i> , 2020, 35, 105023.	2.0	5
38	Formation of ZnO/Zn _{0.5} Cd _{0.5} Se Alloy Quantum Dots in the Presence of High Oleylamine Contents. <i>Nanomaterials</i> , 2019, 9, 999.	4.1	5
39	Deposition of Silicon-Based Stacked Layers for Flexible Encapsulation of Organic Light Emitting Diodes. <i>Nanomaterials</i> , 2019, 9, 1053.	4.1	7
40	Complex Oxides: Quasi-Single-Crystalline ZnGa ₂ O ₄ Films via Solid Phase Epitaxy for Enhancing Deep-Ultraviolet Photoresponse (<i>Adv. Mater. Interfaces</i> 18/2019). <i>Advanced Materials Interfaces</i> , 2019, 6, 1970116.	3.7	0
41	Improved Performance of Deep Ultraviolet Photodetector From Sputtered Ga ₂ O ₃ Films Using Post-Thermal Treatments. <i>IEEE Photonics Journal</i> , 2019, 11, 1-8.	2.0	2
42	Growth and Photocatalytic Properties of Gallium Oxide Films Using Chemical Bath Deposition. <i>Crystals</i> , 2019, 9, 564.	2.2	12
43	Quasi-Single-Crystalline ZnGa ₂ O ₄ Films via Solid Phase Epitaxy for Enhancing Deep-Ultraviolet Photoresponse. <i>Advanced Materials Interfaces</i> , 2019, 6, 1901075.	3.7	13
44	Characteristics of atomic layer deposition-grown zinc oxide thin film with and without aluminum. <i>Applied Surface Science</i> , 2019, 491, 535-543.	6.1	4
45	Effects of growth temperature and thickness on structure and optical properties of Ga ₂ O ₃ films grown by pulsed laser deposition. <i>Superlattices and Microstructures</i> , 2019, 131, 21-29.	3.1	20
46	Enhanced Deep-Ultraviolet Responsivity in Aluminum-Gallium Oxide Photodetectors via Structure Deformation by High-Oxygen-Pressure Pulsed Laser Deposition. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 17563-17569.	8.0	11
47	Surface Treatments on the Characteristics of Metal-Oxide Semiconductor Capacitors. <i>Crystals</i> , 2019, 9, 1.	2.2	50
48	Influence of oxygen on sputtering of aluminum-gallium oxide films for deep-ultraviolet detector applications. <i>Journal of Alloys and Compounds</i> , 2019, 791, 1213-1219.	5.5	18
49	Surface/structural characteristics and band alignments of thin Ga ₂ O ₃ films grown on sapphire by pulse laser deposition. <i>Applied Surface Science</i> , 2019, 479, 1246-1253.	6.1	58
50	Efficiency improvement of PERC solar cell using an aluminum oxide passivation layer prepared via spatial atomic layer deposition and post-annealing. <i>Surface and Coatings Technology</i> , 2019, 358, 968-975.	4.8	21
51	Characterization of aluminum gallium oxide films grown by pulsed laser deposition. <i>Ceramics International</i> , 2019, 45, 702-707.	4.8	15
52	Surface and optical properties of indium-rich InGaIn layers grown on sapphire by migration-enhanced plasma assisted metal organic chemical vapor deposition. <i>Materials Research Express</i> , 2019, 6, 016407.	1.6	4
53	Improved Responsivity Drop From 250 to 200 nm in Sputtered Gallium Oxide Photodetectors by Incorporating Trace Aluminum. <i>IEEE Electron Device Letters</i> , 2018, 39, 220-223.	3.9	46
54	Slow Electron Making More Efficient Radiation Emission. <i>Scientific Reports</i> , 2018, 8, 4865.	3.3	3

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55	Antireflection and passivation property of aluminium oxide thin film on silicon nanowire by liquid phase deposition. <i>Surface and Coatings Technology</i> , 2018, 350, 1058-1064.	4.8	8
56	Zinc oxide-based current spreading layer behavior on the performance of P-side-up thin-film red light emitting diodes. <i>Applied Surface Science</i> , 2018, 432, 196-201.	6.1	6
57	Preparation and Characterization of Sprayed-Yttrium Oxyfluoride Corrosion Protective Coating for Plasma Process Chambers. <i>Coatings</i> , 2018, 8, 373.	2.6	25
58	Structural and Stress Properties of AlGaN Epilayers Grown on AlN-Nanopatterned Sapphire Templates by Hydride Vapor Phase Epitaxy. <i>Nanomaterials</i> , 2018, 8, 704.	4.1	8
59	A New Material and Structures for Light-Emitting Thyristor Applications. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 2904-2908.	3.0	0
60	Growth and characterization of co-sputtered aluminum-gallium oxide thin films on sapphire substrates. <i>Journal of Alloys and Compounds</i> , 2018, 765, 894-900.	5.5	31
61	Tunability of p- and n-channel TiOx thin film transistors. <i>Scientific Reports</i> , 2018, 8, 9255.	3.3	61
62	Surface, structural and optical properties of AlN thin films grown on different face sapphire substrates by metalorganic chemical vapor deposition. <i>Applied Surface Science</i> , 2018, 458, 972-977.	6.1	28
63	Fabrication and Study on Red Light Micro-LED Displays. <i>IEEE Journal of the Electron Devices Society</i> , 2018, 6, 1064-1069.	2.1	50
64	Surface evolution and effect of V/III ratio modulation on etch-pit-density improvement of thin AlN templates on nano-patterned sapphire substrates by metalorganic chemical vapor deposition. <i>Applied Surface Science</i> , 2018, 455, 1123-1130.	6.1	21
65	Effects of high substrate temperature during pulsed laser deposition on the quality of aluminum-doped gallium oxide and its photodetector characteristics. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 070301.	1.5	7
66	Performance of p-side-up thin-film AlGaInP light-emitting diodes with textured composite aluminum-doped zinc oxide transparent conductive layers. <i>Surface and Coatings Technology</i> , 2017, 320, 421-425.	4.8	3
67	High power impulse magnetron sputtered p-type $\hat{3}$ -titanium monoxide films: Effects of substrate bias and post-annealing on microstructure characteristics and optoelectrical properties. <i>Materials Science in Semiconductor Processing</i> , 2017, 61, 85-92.	4.0	12
68	ITO/nano-Ag plasmonic window applied for efficiency improvement of near-ultraviolet light emitting diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600609.	1.8	5
69	Antireflection and passivation property of titanium oxide thin film on silicon nanowire by liquid phase deposition. <i>Surface and Coatings Technology</i> , 2017, 320, 252-258.	4.8	22
70	Chemical lift-off process for nitride LEDs from an Eco-GaN template using an AlN/strip-patterned SiO_2 sacrificial layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600657.	1.8	8
71	Ohmic contact behavior of aluminum-doped zinc oxide with carbon-doped p-GaP epilayer for AlGaInP LEDs applications. <i>Current Applied Physics</i> , 2017, 17, 966-971.	2.4	3
72	Enhanced Light Extraction of High-Voltage Light Emitting Diodes Using a Sidewall Chamfer Structure. <i>IEEE Photonics Journal</i> , 2017, 9, 1-9.	2.0	4

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73	Improved Performance and Heat Dissipation of Flip-Chip White High-Voltage Light Emitting Diodes. IEEE Transactions on Device and Materials Reliability, 2017, 17, 197-203.	2.0	7
74	Transformation from Film to Nanorod via a Sacrificial Layer: Pulsed Laser Deposition of ZnO for Enhancing Photodetector Performance. Scientific Reports, 2017, 7, 14251.	3.3	13
75	85% internal quantum efficiency of 280-nm AlGaIn multiple quantum wells by defect engineering. Scientific Reports, 2017, 7, 14422.	3.3	43
76	Improved Optoelectronic Performance of High-Voltage Ultraviolet Light-Emitting Diodes Through Electrode Designs. IEEE Transactions on Electron Devices, 2017, 64, 4526-4531.	3.0	9
77	A Low-Temperature External Electron Retarding Electrode for Improving Vertical Green LED Performance. IEEE Transactions on Electron Devices, 2017, 64, 3219-3225.	3.0	0
78	Reduction of Defects in AlGaIn Grown on Nanoscale-Patterned Sapphire Substrates by Hydride Vapor Phase Epitaxy. Materials, 2017, 10, 605.	2.9	5
79	Comparison of Erosion Behavior and Particle Contamination in Mass-Production CF ₄ /O ₂ Plasma Chambers Using Y ₂ O ₃ and YF ₃ Protective Coatings. Nanomaterials, 2017, 7, 183.	4.1	47
80	Optoelectronic Properties and Structural Characterization of GaN Thick Films on Different Substrates through Pulsed Laser Deposition. Applied Sciences (Switzerland), 2017, 7, 87.	2.5	10
81	Improved Performance of High-Voltage Vertical GaN LEDs via Modification of Micro-Cell Geometry. Applied Sciences (Switzerland), 2017, 7, 506.	2.5	3
82	On the Role of AlN Insertion Layer in Stress Control of GaN on 150-mm Si (111) Substrate. Crystals, 2017, 7, 134.	2.2	13
83	AlGaIn/GaN MOS-HEMTs with Corona-Discharge Plasma Treatment. Crystals, 2017, 7, 146.	2.2	5
84	Effect of Top-Region Area of Flat-Top Pyramid Patterned Sapphire Substrate on the Optoelectronic Performance of GaN-Based Light-Emitting Diodes. Journal of Nanomaterials, 2016, 2016, 1-8.	2.7	1
85	Enhanced light extraction in wafer-bonded p-side-up thin-film AlGaInP light emitting diodes via zinc oxide nanorods. Optical Materials Express, 2016, 6, 3293.	3.0	5
86	On the role of diluted magnetic cobalt-doped ZnO electrodes in efficiency improvement of InGaIn light emitters. Applied Physics Letters, 2016, 109, 021110.	3.3	2
87	Characteristics of yttrium fluoride and yttrium oxide coatings for plasma process equipment prepared by atmospheric plasma spraying. Japanese Journal of Applied Physics, 2016, 55, 126201.	1.5	23
88	Performance of Flexible Photovoltaic Modules Encapsulated by Silicon Oxide/Organic Silicon Stacked Layers. IEEE Transactions on Electron Devices, 2016, 63, 1615-1620.	3.0	6
89	Surface passivation property of aluminum oxide thin film on silicon substrate by liquid phase deposition. Thin Solid Films, 2016, 618, 118-123.	1.8	12
90	Performance comparison of p-side-up thin-film AlGaInP light emitting diodes with aluminum-doped zinc oxide and indium tin oxide transparent conductive layers. Optical Materials Express, 2016, 6, 1349.	3.0	9

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91	Effect of the Phosphor Permanent Substrate on the Angular CCT for White Thin-Film Flip-Chip Light-Emitting Diodes. IEEE Transactions on Electron Devices, 2016, 63, 3977-3982.	3.0	3
92	Fabrication of nitride LEDs using chemical lift-off from a GaN/sapphire template. , 2016, , .		0
93	Co-doped ZnO dilute magnetic semiconductor thin films by pulsed laser deposition: Excellent transmittance, low resistivity and high mobility. Journal of Alloys and Compounds, 2016, 663, 107-115.	5.5	28
94	Controlling the stress of growing GaN on 150-mm Si (111) in an AlN/GaN strained layer superlattice. Applied Surface Science, 2016, 362, 434-440.	6.1	17
95	Influence of Surface Morphology on the Effective Lifetime and Performance of Silicon Heterojunction Solar Cell. International Journal of Photoenergy, 2015, 2015, 1-8.	2.5	12
96	Silicon films deposited on flexible substrate by hot-wire chemical-vapor deposition. Vacuum, 2015, 118, 109-112.	3.5	3
97	A High-Temperature Die-Bonding Structure Fabricated at Low Temperature for Light-Emitting Diodes. IEEE Electron Device Letters, 2015, 36, 835-837.	3.9	10
98	External stress effects on the optical and electrical properties of flexible InGaN-based green light-emitting diodes. Optics Express, 2015, 23, 31334.	3.4	13
99	InGaN LED fabricated on Eco-GaN template with a Ga ₂ O ₃ sacrificial layer for chemical lift-off application. Vacuum, 2015, 118, 8-12.	3.5	12
100	Properties of double-layer Al ₂ O ₃ /TiO ₂ antireflection coatings by liquid phase deposition. Thin Solid Films, 2015, 584, 248-252.	1.8	31
101	Hot-wire chemical vapor deposition of nanocrystalline silicon for ambipolar thin-film transistor applications. Applied Surface Science, 2015, 354, 216-220.	6.1	8
102	Transparent Conductive Oxide Films Embedded with Plasmonic Nanostructure for Light-Emitting Diode Applications. ACS Applied Materials & Interfaces, 2015, 7, 2546-2553.	8.0	31
103	Pulsed laser deposition of gallium oxide films for high performance solar-blind photodetectors. Optical Materials Express, 2015, 5, 1240.	3.0	155
104	Effect of the polymer overcoat on the performance of the SiN _x /SiO _x multilayer barrier for OLED gas barrier applications. , 2015, , .		0
105	Structural, Surface Morphology and Optical Properties of ZnS Films by Chemical Bath Deposition at Various Zn/S Molar Ratios. Journal of Nanomaterials, 2014, 2014, 1-7.	2.7	14
106	Texture-Etched SnO ₂ Glasses Applied to Silicon Thin-Film Solar Cells. Journal of Nanomaterials, 2014, 2014, 1-9.	2.7	1
107	Self-textured oxide structure for improved performance of 365 nm ultraviolet vertical-type light-emitting diodes. Optics Express, 2014, 22, 17600.	3.4	5
108	Performance of GaN-based light-emitting diodes fabricated using GaN epilayers grown on silicon substrates. Optics Express, 2014, 22, A179.	3.4	16

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109	Analysis of the Thickness Effect of Undoped Electron-Blocking Layer in Ultraviolet LEDs. IEEE Transactions on Electron Devices, 2014, 61, 3790-3795.	3.0	7
110	Improvement in performance of Si-based thin film solar cells with a nanocrystalline SiO ₂ /TiO ₂ layer. Thin Solid Films, 2014, 570, 200-203.	1.8	5
111	Performance of a-SiGe:H Thin-Film Solar Cells on High-Heat Dissipation Flexible Ceramic Printable Circuit Board. IEEE Transactions on Electron Devices, 2014, 61, 3125-3130.	3.0	2
112	Effect of Plasma Radical Composition in Intrinsic a-Si:H on Performances of Heterojunction Solar Cells. IEEE Transactions on Plasma Science, 2014, 42, 3786-3791.	1.3	1
113	Improved Performance of 365-nm LEDs by Inserting an Un-Doped Electron-Blocking Layer. IEEE Electron Device Letters, 2014, 35, 467-469.	3.9	10
114	Performance of Cu-Plating Vertical LEDs in Heat Dissipation Using Diamond-Like Carbon. IEEE Electron Device Letters, 2014, 35, 169-171.	3.9	3
115	Highly Stable Micromorph Tandem Solar Cells Fabricated by ECRCVD With Separate Silane Gas Inlets System. IEEE Journal of Quantum Electronics, 2014, 50, 515-521.	1.9	4
116	Metal chloride precursor synthesization of Cu ₂ ZnSnS ₄ solar cell materials. Journal of the Korean Physical Society, 2014, 65, 196-199.	0.7	1
117	ZnO Nanowires Embedded in Epoxy Resin Separating from the Substrate for Wearable Electronics Applications. IEEE Nanotechnology Magazine, 2014, 13, 458-463.	2.0	9
118	Lattice deformation of wurtzite Mg _{1-x} Zn _x O alloys: An extended X-ray absorption fine structure study. Journal of Alloys and Compounds, 2014, 582, 157-160.	5.5	11
119	Improved GaN-on-Si epitaxial quality by incorporating various Si _x N _y interlayer structures. Journal of Crystal Growth, 2014, 399, 27-32.	1.5	13
120	Effect of oxygen to argon flow ratio on the properties of Al-doped ZnO films for amorphous silicon thin film solar cell applications. Thin Solid Films, 2013, 529, 50-53.	1.8	6
121	ZnO nanowires lift-off from silicon substrate embedded in flexible films. , 2013, , .		0
122	Thin Film GaN LEDs Using a Patterned Oxide Sacrificial Layer by Chemical Lift-Off Process. IEEE Photonics Technology Letters, 2013, 25, 2435-2438.	2.5	14
123	An 83% enhancement in the external quantum efficiency of ultraviolet flip-chip light-emitting diodes with the incorporation of a self-textured oxide mask. IEEE Electron Device Letters, 2013, 34, 274-276.	3.9	21
124	Thermal annealing effect on material characterizations of In^{2-} -Ga ₂ O ₃ epilayer grown by metal organic chemical vapor deposition. Applied Physics Letters, 2013, 102, .	3.3	67
125	Modified cone shapes on patterned sapphire substrates for high performance InGaN LED applications. , 2013, , .		0
126	Effect of non-vacuum thermal annealing on high indium content InGaN films deposited by pulsed laser deposition. Optics Express, 2013, 21, 7337.	3.4	8

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127	High performance of Ga-doped ZnO transparent conductive layers using MOCVD for GaN LED applications. Optics Express, 2013, 21, 14452.	3.4	38
128	P-side up AlGaInP-based light emitting diodes with dot-patterned GaAs contact layers. Optics Express, 2013, 21, 19668.	3.4	16
129	Effect of Hydrogen Content in Intrinsic a-Si:H on Performances of Heterojunction Solar Cells. International Journal of Photoenergy, 2013, 2013, 1-6.	2.5	5
130	Fabrication of an Ultra-Flexible ZnO Nanogenerator for Harvesting Energy from Respiration. ECS Journal of Solid State Science and Technology, 2013, 2, P400-P404.	1.8	25
131	Effect of Different Patterns Epitaxial Lift-Off Process by Finite Element Method. ECS Transactions, 2013, 53, 295-301.	0.5	0
132	Growth and Characterization of Single Crystalline Ga-doped ZnO Thin Films Using Metal-Organic Chemical Vapor Deposition. ECS Transactions, 2013, 53, 3-9.	0.5	0
133	An Efficient Metal-Core Printed Circuit Board With a Copper-Filled Through (Blind) Hole for Light-Emitting Diodes. IEEE Electron Device Letters, 2013, 34, 105-107.	3.9	9
134	Pulsed laser deposition of hexagonal GaN-on-Si(100) template for MOCVD applications. Optics Express, 2013, 21, 26468.	3.4	25
135	Characterization of Nanocrystalline SiGe Thin Film Solar Cell with Double Graded-Dead Absorption Layer. International Journal of Photoenergy, 2012, 2012, 1-6.	2.5	6
136	High thermal stability of high indium content InGaN films grown by pulsed laser deposition. Optics Express, 2012, 20, 21173.	3.4	12
137	High indium content InGaN films grown by pulsed laser deposition using a dual-compositing target. Optics Express, 2012, 20, 15149.	3.4	16
138	Effect of diamond like carbon layer on heat dissipation and optoelectronic performance of vertical-type InGaN light emitting diodes. Applied Physics Letters, 2012, 101, .	3.3	13
139	Optimization of textured structure on crystalline silicon wafer for heterojunction solar cell. Materials Chemistry and Physics, 2012, 133, 63-68.	4.0	26
140	Growth and etching characteristics of gallium oxide thin films by pulsed laser deposition. Materials Chemistry and Physics, 2012, 133, 700-705.	4.0	100
141	Improvement of thermal management of high-power GaN-based light-emitting diodes. Microelectronics Reliability, 2012, 52, 861-865.	1.7	59
142	Hot-wire chemical vapor deposition and characterization of p-type nanocrystalline SiC films and their use in Si heterojunction solar cells. Thin Solid Films, 2012, 520, 2110-2114.	1.8	14
143	Hot-wire chemical vapor deposition and characterization of p-type nanocrystalline Si films for thin film photovoltaic applications. Thin Solid Films, 2012, 520, 5200-5205.	1.8	12
144	Direct growth of large grain polycrystalline silicon films on aluminum-induced crystallization seed layer using hot-wire chemical vapor deposition. Thin Solid Films, 2012, 520, 5860-5866.	1.8	22

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145	Crystalline quality and photovoltaic performance of InGaAs solar cells grown on GaAs substrate with large-misoriented angle. <i>Vacuum</i> , 2012, 86, 843-847.	3.5	5
146	Demonstration of InGaN Light-Emitting Diodes by Incorporating a Self-Textured Oxide Mask Structure. <i>IEEE Photonics Technology Letters</i> , 2011, 23, 1240-1242.	2.5	4
147	Surface Modification on Wet-Etched Patterned Sapphire Substrates Using Plasma Treatments for Improved GaN Crystal Quality and LED Performance. <i>Journal of the Electrochemical Society</i> , 2011, 158, H988.	2.9	34
148	Light Extraction Investigation for Thin-Film GaN Light-Emitting Diodes With Imbedded Electrodes. <i>IEEE Photonics Technology Letters</i> , 2011, 23, 54-56.	2.5	7
149	Transferring Thin Film GaN LED Epi-Structure to the Cu Substrate by Chemical Lift-Off Technology. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, H281-H284.	2.2	9
150	Study of 375-nm ultraviolet InGaN/AlGaN light-emitting diodes with heavily Si-doped GaN transition layer in growth mode, internal quantum efficiency, and device performance. <i>Journal of Applied Physics</i> , 2011, 110, 123102.	2.5	8
151	Hot-wire chemical vapor deposition and characterization of polycrystalline silicon thin films using a two-step growth method. <i>Materials Chemistry and Physics</i> , 2011, 126, 665-668.	4.0	6
152	Effect of Crystalline Quality on Photovoltaic Performance for $\text{In}_{0.17}\text{Ga}_{0.83}\text{As}$ Solar Cell Using X-Ray Reciprocal Space Mapping. <i>IEEE Journal of Quantum Electronics</i> , 2011, 47, 1434-1442.	1.9	11
153	Enhanced Output Power of Near-Ultraviolet InGaN/AlGaN LEDs With Patterned Distributed Bragg Reflectors. <i>IEEE Transactions on Electron Devices</i> , 2011, 58, 173-179.	3.0	20
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